

Warner-Jenkinson Co. v. Hilton Davis Chemical Co., 41 USPQ2d 1865, 1873 (1997).

Please amend the following claims:

(1) Please amend claim 1 as follows:

- DS
- 1 1. (Thrice Amended) A method for providing a halo implant to a
2 semiconductor device comprising the steps of:
3 (a) providing a thin photoresist layer to the semiconductor device that
4 covers a substantial amount of an active area comprising a source region and a drain
5 region of the semiconductor device; and
6 (b) providing the halo implant to the semiconductor device, wherein the
7 thin photoresist layer is used as a mask.

(2) Please amend claim 8 as follows:

- D6
- 1 8. (Fourth Amended) A system for providing a halo implant to a
2 semiconductor device comprising:
3 means for providing a thin photoresist layer to the semiconductor device,
4 wherein the thin photoresist layer covers a substantial amount of an active area
5 comprising a source region and a drain region of the semiconductor device; and
6 means for providing the halo implant to the semiconductor device, wherein
7 the thin photoresist layer is used as a mask.

IN THE DRAWINGS

A corrected version of Figure 2 is submitted herewith on a separate sheet with corrections marked in red ink. Applicants have labeled element 202 as discussed in the specification and properly labeled element 204 as corresponding to a source region rather than a drain region in semiconductor device 200. Applicants